

Atty Docket No. CPH35726-D1-R

Serial No. 10/072,362

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-9 (canceled).

10. (currently amended) A semiconductor structure comprising a substrate having an active region of a first conductive type including a channel region and a non-channel region surrounding the channel region, at least a first trench and a second trench disposed in the active region, the structure comprising:

a thick insulating layer disposed over said first and second trench, ~~the thick insulating layer~~ partially filling said first and second trench profile and being conformal to said first and second trench profile;

a gate electrode disposed over said thick insulating layer in said first and second trenches, the gate electrode comprising a first vertical portion, a second vertical portion and a horizontal portion, wherein the first vertical portion is embedded inside the first trench and said thick insulating layer and said first vertical portion within the first trench completely fills filling a remaining portion of the first trench, the second vertical portion is embedded inside the second trench and said thick insulating layer and said second vertical portion within the first trench completely fills filling a remaining portion of the second trench, and the horizontal portion is disposed over the substrate and connects said first and second vertical portions together; and

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a first shallow doped region within the substrate disposed at an upper corner adjacent to the first vertical portion and a second shallow doped region disposed at an upper corner adjacent to the second vertical portion of the electrode; and

a first deep source region extending from the first shallow doped region and a second deep drain region extending from the second shallow doped region are disposed in a region within the substrate deeper than the first and second trenches.

11. (previously presented) The structure according to claim 10, wherein the thick insulating layer is formed by thermal oxidation.

12. (previously presented) The structure according to claim 10, wherein the a thickness of the thick insulating layer is about 0.1 μm .

13. (currently amended) A semiconductor structure comprising a substrate having an active region of a first conductive type including a channel region and a non-channel region surrounding the channel region, at least a first trench and a second trench disposed in the active region, the structure comprising:

a thick insulating layer disposed over said first and second trench, the thick insulating layer being conformal to said first and second trench profile; and

a gate electrode disposed over said first and second trenches, the gate electrode comprising a first vertical portion, a second vertical portion and a horizontal portion, wherein the first vertical portion is embedded inside the first trench and said thick insulating layer and said first vertical portion within the first trench completely fills the first

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trench, the second vertical portion is embedded inside the second trench and said thick insulating layer and said second vertical portion within the second trench completely fills the second trench, and the horizontal portion is disposed over the substrate and connects said first and second vertical portions together; and

~~— a first shallow doped region having dopants of first type within the substrate disposed at an upper corner adjacent to the first vertical portion and a second shallow doped region having dopants of first type disposed at an upper corner adjacent to the second vertical portion of the electrode; and~~

~~— a first deep source region having dopants of second type extending from the first shallow doped region and a second deep drain region having dopants of second type extending from the second shallow doped region are disposed in a region within the substrate deeper than the first and second trenches.~~

14. (previously presented) The structure according to claim 13, wherein the thick insulating layer is formed by thermal oxidation.

15. (previously presented) The structure according to claim 13, wherein the a thickness of the thick insulating layer is about 0.1 μm .

Claims 16-18 (canceled).